

REMARKS

Claims 20, 28-31, 33-45, 47-53, 55 and 56 are pending in this application, with claims 20, 34, 41 and 49 being independent. Claims 20 and 34 have each been amended to recite additional features that clarify the structure of the recess defined by the semiconductor layer (claims 20 and 34) and the second recess defined by the anodic oxide (claim 34), as shown, for example, in Fig. 3C of the application. No new matter has been introduced.

Independent claims 20, 34, 41 and 49, and their dependent claims 28, 31, 35, 38, 42, 45, 47, 50, 53 and 55, have been rejected as being anticipated by Kudoh (U.S. Patent No. 5,159,416). Applicants responded to this rejection in the response filed on October 31, 2007. The present amendment to claims 20 and 34 helps to further distinguish these claims, and their dependent claims, from the teachings of Kudoh.

In particular, applicants amended each of claims 20 and 34 to recite "a gate insulating film on and in contact with the semiconductor layer, the gate insulating film defining a first contact hole extending from a first opening located at a top surface of the gate insulating film to a second opening located at a bottom surface of the gate insulating film, and the semiconductor layer defining a [first] recess having a third opening located at a top surface of the semiconductor layer that is in communication with the second opening, the third opening defining an area that is greater than an area defined by the second opening such that a portion of the gate insulating film extends over a portion of the [first] recess." Applicants submit that Kudoh does not describe or suggest the above features and, therefore, applicants request reconsideration and withdrawal of the rejection of claims 20 and 34, and their dependent claims.

Kudoh describes a TFT structure having a shottky barrier that includes a silicon film 12, which the Examiner equates to the recited semiconductor layer, on which is formed a titanium silicide film 15, which the Examiner equates to the recited side recess. As stated in the response of October 31, applicants submit that titanium silicide film 15 is a film and, therefore, is not a recess. Assuming, for the sake of argument, that the portion of the silicon film 12 on which the titanium silicide film 15 is formed were somehow construed to be a recess, applicants submit that this recess is not a recess having a third opening located at a top surface of the semiconductor layer that is in communication with a second opening located at a bottom surface of a gate

insulating film, the third opening defining an area that is greater than an area defined by the second opening such that a portion of the gate insulating film extends over a portion of the recess, as claimed.

For at least this reason, applicants request reconsideration and withdrawal of the rejection of claims 20 and 34, and their dependent claims.

With respect to the rejections of the other claims in the Final Office Action, applicants reiterate the reasons submitted in the response filed on October 31, 2007 in support of applicants' request for withdrawal of these rejections. Specifically, regarding the rejections of independent claims 41 and 49, applicants note that each of claims 41 and 49 recites a source electrode that contains a first layer and a second layer, wherein a part of each of the first and second layers is located over an interlayer insulating film. As stated previously, titanium silicide film 15, which the Examiner also equates to the recited first layer, is not located over an interlayer insulating film. Rather, it is located over silicon film 12. For at least this reason, applicants request reconsideration and withdrawal of the rejection of claims 41 and 49, and their dependent claims.

Applicants submit that all claims are in condition for allowance.

No fees are believed due in connection with this filing. If any fees or refunds are due, please apply any charges or credits to deposit account 06-1050.

Respectfully submitted,



Roberto J. Devoto
Reg. No. 55,108

Date: December 13, 2007

Fish & Richardson P.C.
1425 K Street, N.W.
11th Floor
Washington, DC 20005-3500
Telephone: (202) 783-5070
Facsimile: (202) 783-2331